

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

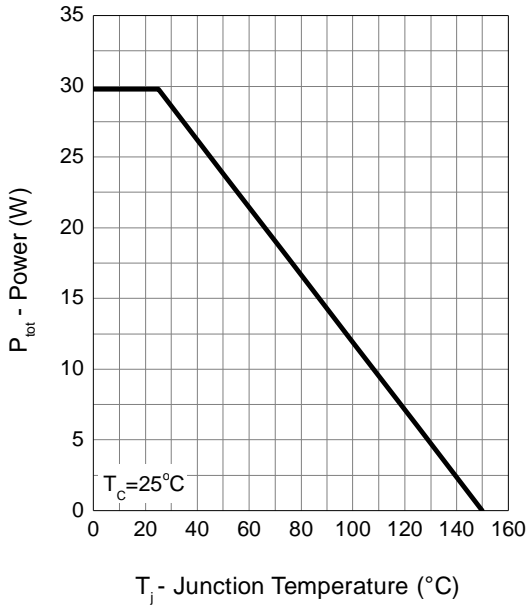
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24V, V_{GS}=0V$ $T_j=85^\circ\text{C}$	-	-	-1	μA
			-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-1.0	-1.5	-2.0	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	± 100	nA
$R_{DS(ON)}^c$	Drain-Source On-state Resistance	$V_{GS}=-10V, I_{DS}=-16A$	-	16	21	m Ω
		$V_{GS}=-4.5V, I_{DS}=-8A$	-	22	32	
Body Diode Characteristics						
V_{SD}^c	Diode Forward Voltage	$I_{SD}=-1A, V_{GS}=0V$	-	-0.7	-1.0	V
t_{rr}^d	Reverse Recovery Time	$I_{DS}=-16A,$ $dI_{SD}/dt=100A/\mu s$	-	18	-	ns
Q_{rr}^d	Reverse Recovery Charge		-	9	-	nC
Dynamic Characteristics						
R_G	Gate Resistance	$F=1\text{MHz}, V_{GS}=0V$	-	4	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=-15V,$ Frequency=1.0MHz	-	1080	-	pF
C_{oss}	Output Capacitance		-	220	-	
C_{rss}	Reverse transfer capacitance		-	170	-	
$t_{d(ON)}$	Turn-on delay Time	$V_{GS}=-10V, V_{DS}=-15V$ $R_G=6\Omega, I_D=-1A, R_L=15\Omega$	-	11.2	-	nS
t_r	Turn-on rise Time		-	10.6	-	
$t_{d(OFF)}$	Turn-off delay Time		-	37	-	
t_f	Turn-off rise Time		-	50	-	
Gate Charge Characteristics						
Q_g	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-10V,$ $I_{DS}=-16A$	-	20	-	nC
Q_{gs}	Gate-Source Charge		-	1.1	-	
Q_{gd}	Gate-Drain Charge		-	7.7	-	

Note c : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

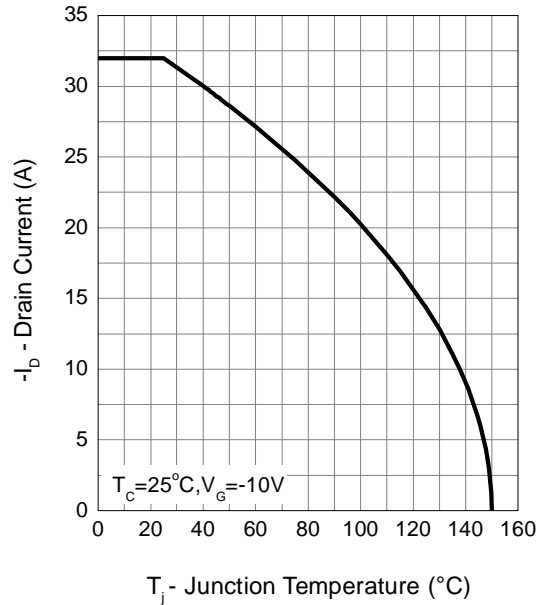
Note d : Guaranteed by design, not subject to production testing.

Typical Characteristics

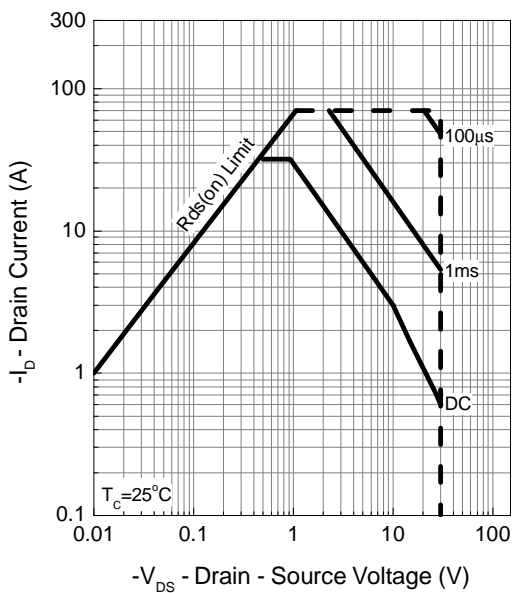
Power Dissipation



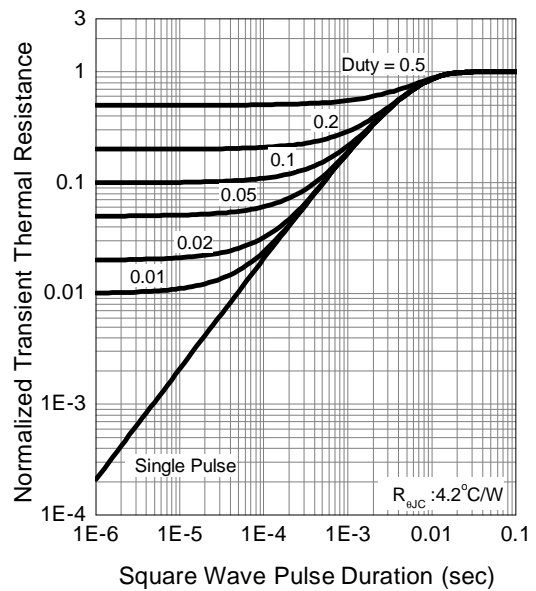
Drain Current



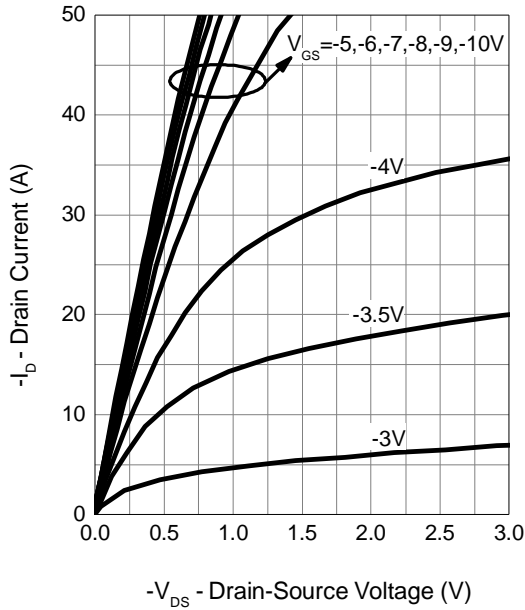
Safe Operation Area



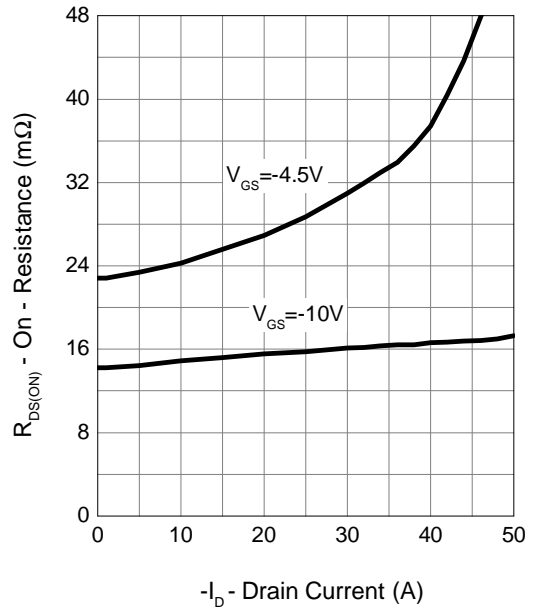
Thermal Transient Impedance



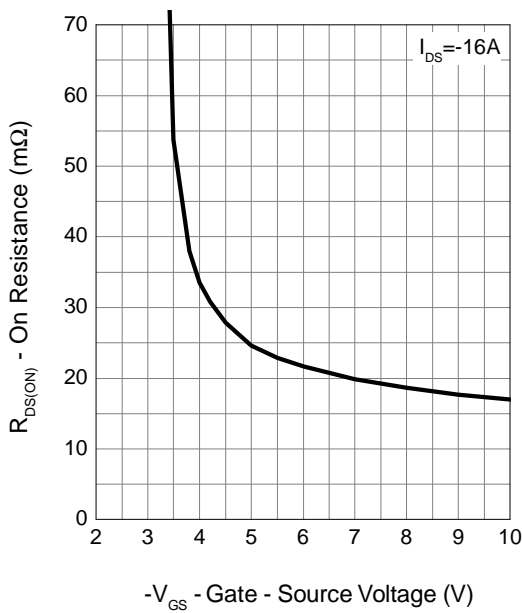
Output Characteristics



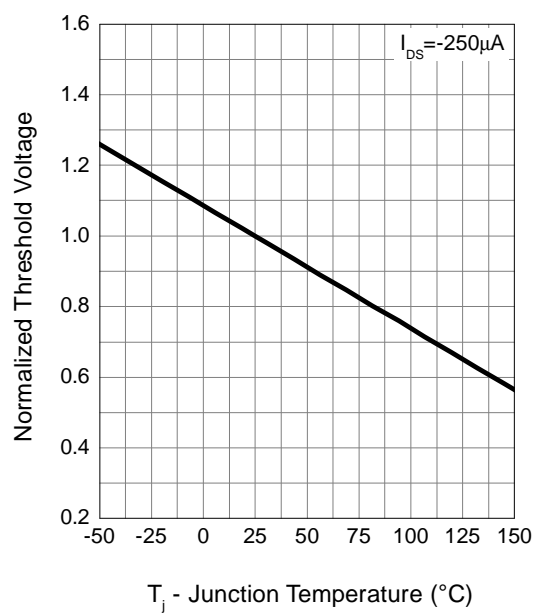
Drain-Source On Resistance



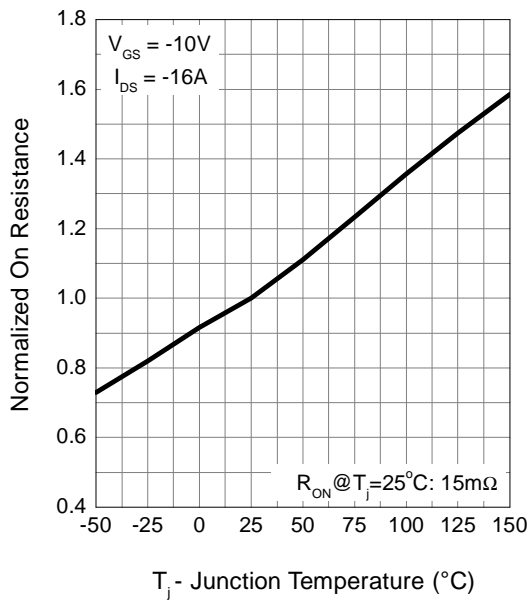
Gate-Source On Resistance



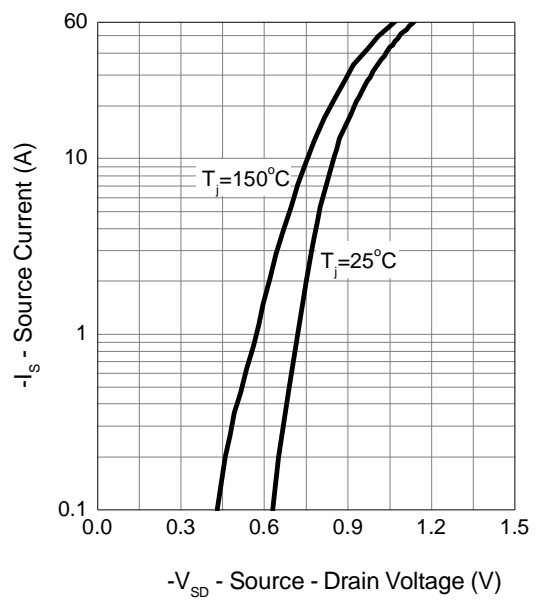
Gate Threshold Voltage



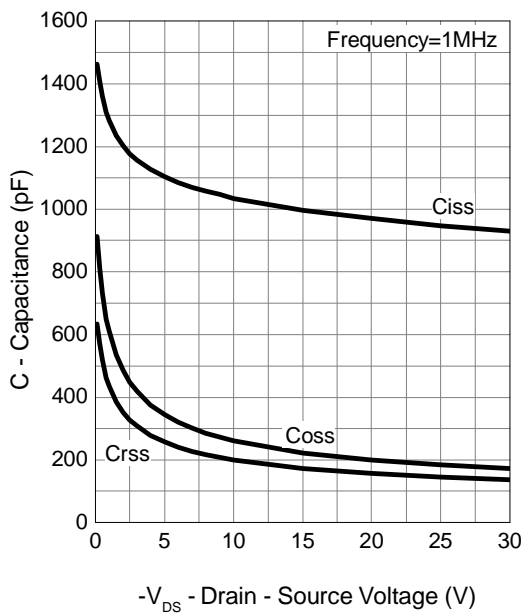
Drain-Source On Resistance



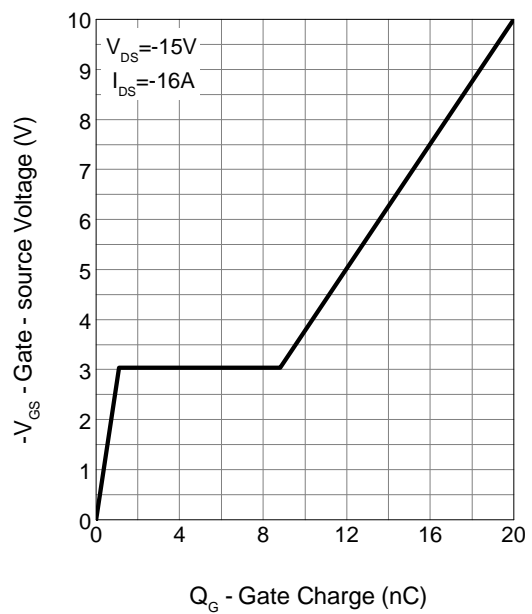
Source-Drain Diode Forward



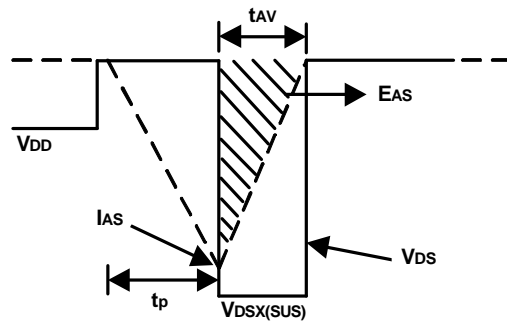
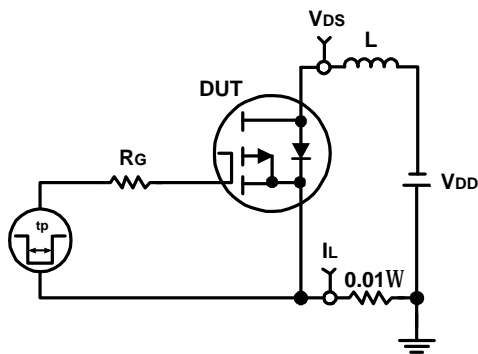
Capacitance



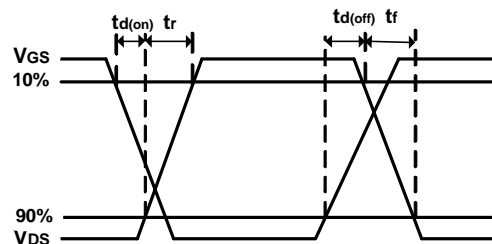
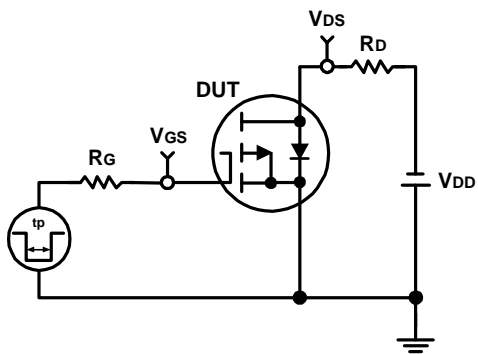
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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